

# Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceed the OCM data sheet.

# **Quality Overview**

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-35835
  - Class Q Military
  - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)
- Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

# Retriggerable Monostable Multivibrators

These dc triggered multivibrators feature pulse width control by three methods. The basic pulse width is programmed by selection of external resistance and capacitance values. The LS122 has an internal timing resistor that allows the circuits to be used with only an external capacitor. Once triggered, the basic pulse width may be extended by retriggering the gated low-level-active (A) or high-level-active (B) inputs, or be reduced by use of the overriding clear.

- Overriding Clear Terminates Output Pulse
- Compensated for V<sub>CC</sub> and Temperature Variations
- DC Triggered from Active-High or Active-Low Gated Logic Inputs
- Retriggerable for Very Long Output Pulses, up to 100% Duty Cycle
- Internal Timing Resistors on LS122

### **GUARANTEED OPERATING RANGES**

Symbol	Parameter	Min	Тур	Max	Unit
V <sub>CC</sub>	Supply Voltage	4.75	5.0	5.25	V
T <sub>A</sub>	Operating Ambient Temperature Range	0	25	70	လိ
I <sub>OH</sub>	Output Current - High			-0.4	mA
I <sub>OL</sub>	Output Current – Low			8.0	mA
R <sub>ext</sub>	External Timing Resistance	5.0		260	kΩ
C <sub>ext</sub>	External Capacitance		No Res	striction	19
R <sub>ext</sub> /C <sub>ext</sub>	Wiring Capacitance at R <sub>ext</sub> /C <sub>ext</sub> Terminal			50	pF
	PLEA	A.E.	PE	SER .	



# ON Semiconductor™

http://onsemi.com

# LOW POWER SCHOTTKY



PLASTIC N SUFFIX CASE 646



SOIC D SUFFIX CASE 751A



PLASTIC N SUFFIX CASE 648



SOIC D SUFFIX CASE 751B



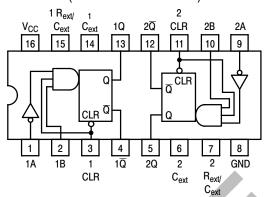
SOEIAJ M SUFFIX CASE 966

### **ORDERING INFORMATION**

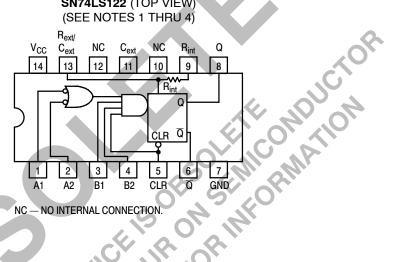
Device	Package	Shipping
SN74LS122N	14 Pin DIP	2000 Units/Box
SN74LS122D	SOIC-14	55 Units/Rail
SN74LS122DR2	SOIC-14	2500/Tape & Reel
SN74LS123N	16 Pin DIP	2000 Units/Box
SN74LS123D	SOIC-16	38 Units/Rail
SN74LS123DR2	SOIC-16	2500/Tape & Reel
SN74LS123M	SOEIAJ-16	See Note 1
SN74LS123MEL	SOEIAJ-16	See Note 1

For ordering information on the EIAJ version of the SOIC package, please contact your local ON Semiconductor representative.

## SN74LS123 (TOP VIEW) (SEE NOTES 1 THRU 4)



# SN74LS122 (TOP VIEW) (SEE NOTES 1 THRU 4)



NC - NO INTERNAL CONNECTION.

# NOTES:

- 1. An external timing capacitor may be connected between  $C_{\text{ext}}$  and  $R_{\text{ext}}/C_{\text{ext}}$  (positive).
- 2. To use the internal timing resistor of the LS122, connect R<sub>int</sub> to V<sub>CC</sub>.

  3. For improved pulse width accuracy connect an external resistor between R<sub>ext</sub>/C<sub>ext</sub> and V<sub>CC</sub> with R<sub>int</sub> open-circuited.
- 4. To obtain variable pulse widths, connect an external variable resistance between Rint/Cext and VCC.

#### **LS122 FUNCTIONAL TABLE**

	INPUTS					
CLEAR	<b>A</b> 1	A2	B1	B2	Q	Q
L	Χ	Χ	Χ	Χ	L	Н
X	Н	Н	Χ	X	L	Н
X	Х	Χ	L	Χ	L	Н
X	Х	Χ	Χ	L	L	Н
Н	L	Χ	1	Н	л	ъ
Н	L	Χ	Н	<b>↑</b>	л	ъ
Н	Х	L	1	Н	л	ъ
Н	Х	L	Н	1	л	ъ
Н	Н	$\downarrow$	Н	Н	л	ъ
Н	$\downarrow$	$\downarrow$	Н	Н	л	ъ
Н	$\downarrow$	Н	Н	Н	л	T
1	L	X	Н	Н	Т	ъ
1	Х	L	Н	Н	Т	ъ

# TYPICAL APPLICATION DATA

The output pulse  $t_W$  is a function of the external components,  $C_{ext}$  and  $R_{ext}$  or  $C_{ext}$  and  $R_{int}$  on the LS122. For values of  $C_{ext} \ge 1000$  pF, the output pulse at  $V_{CC} = 5.0$  V and  $V_{RC} = 5.0$  V (see Figures 1, 2, and 3) is given by

$$t_W = K R_{ext} C_{ext}$$
 where K is nominally 0.45

If  $C_{ext}$  is on pF and  $R_{ext}$  is in  $k\Omega$  then  $t_W$  is in nanoseconds. The  $C_{ext}$  terminal of the LS122 and LS123 is an internal connection to ground, however for the best system performance  $C_{ext}$  should be hard-wired to ground.

Care should be taken to keep  $R_{ext}$  and  $C_{ext}$  as close to the monostable as possible with a minimum amount of inductance between the  $R_{ext}/C_{ext}$  junction and the  $R_{ext}/C_{ext}$  pin. Good groundplane and adequate bypassing should be designed into the system for optimum performance to ensure that no false triggering occurs.

It should be noted that the  $C_{\rm ext}$  pin is internally connected to ground on the LS122 and LS123, but not on the LS221. Therefore, if  $C_{\rm ext}$  is hard-wired externally to ground, substitution of a LS221 onto a LS123 socket will cause the LS221 to become non-functional.

The switching diode is not needed for electrolytic capacitance application and should not be used on the LS122 and LS123.

To find the value of K for  $C_{ext} \ge 1000$  pF, refer to Figure 4. Variations on  $V_{CC}$  or  $V_{RC}$  can cause the value of K to change, as can the temperature of the LS123, LS122.

**LS123 FUNCTIONAL TABLE** 

INI	OUT	PUTS		
CLEAR	Α	В	Q	Q
L	Х	Х	L	Н
X	Н	Χ	L	Н
X	Х	L	L	Н
Н	L	1	л	ப
Н	↓	Н	л	ъ
1	L	Н	Л	ъ

Figures 5 and 6 show the behavior of the circuit shown in Figures 1 and 2 if separate power supplies are used for  $V_{CC}$  and  $V_{RC}$ . If  $V_{CC}$  is tied to  $V_{RC}$ , Figure 7 shows how K will vary with  $V_{CC}$  and temperature. Remember, the changes in  $R_{ext}$  and  $C_{ext}$  with temperature are not calculated and included in the graph.

As long as  $C_{ext} \ge 1000$  pF and  $5K \le R_{ext} \le 260K$ , the change in K with respect to  $R_{ext}$  is negligible.

If  $C_{ext} \le 1000$  pF the graph shown on Figure 8 can be used to determine the output pulse width. Figure 9 shows how K will change for  $C_{ext} \le 1000$  pF if  $V_{CC}$  and  $V_{RC}$  are connected to the same power supply. The pulse width  $t_W$  in nanoseconds is approximated by

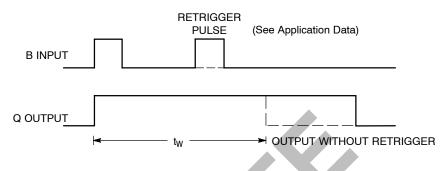
$$t_W = 6 + 0.05 C_{ext} (pF) + 0.45 R_{ext} (k\Omega) C_{ext} + 11.6 R_{ext}$$

In order to trim the output pulse width, it is necessary to include a variable resistor between  $V_{CC}$  and the  $R_{ext}/C_{ext}$  pin or between  $V_{CC}$  and the  $R_{ext}$  pin of the LS122. Figure 10, 11, and 12 show how this can be done.  $R_{ext}$  remote should be kept as close to the monostable as possible.

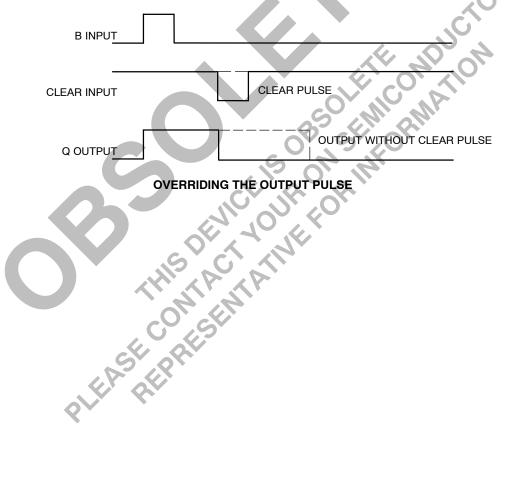
Retriggering of the part, as shown in Figure 3, must not occur before  $C_{ext}$  is discharged or the retrigger pulse will not have any effect. The discharge time of  $C_{ext}$  in nanoseconds is guaranteed to be less than 0.22  $C_{ext}$  (pF) and is typically 0.05  $C_{ext}$  (pF).

For the smallest possible deviation in output pulse widths from various devices, it is suggested that  $C_{ext}$  be kept  $\geq 1000$  pF.

### **WAVEFORMS**



# **EXTENDING PULSE WIDTH**



# DC CHARACTERISTICS OVER OPERATING TEMPERATURE RANGE (unless otherwise specified)

				Limits				
Symbol	Parameter		Min	Тур	Max	Unit	Test C	onditions
V <sub>IH</sub>	Input HIGH Voltage		2.0			V	Guaranteed Inp All Inputs	ut HIGH Voltage for
V <sub>IL</sub>	Input LOW Voltage				0.8	V	Guaranteed Inp All Inputs	ut LOW Voltage for
V <sub>IK</sub>	Input Clamp Diode Voltage			-0.65	-1.5	V	V <sub>CC</sub> = MIN, I <sub>IN</sub> =	= –18 mA
V <sub>OH</sub>	Output HIGH Voltage		2.7	3.5		V	V <sub>CC</sub> = MIN, I <sub>OH</sub> or V <sub>IL</sub> per Truth	= MAX, V <sub>IN</sub> = V <sub>IH</sub> Table
.,,	0 12 11 0 11 0 11 12 12			0.25	0.4	V	I <sub>OL</sub> = 4.0 mA	V <sub>CC</sub> = V <sub>CC</sub> MIN,
V <sub>OL</sub>	Output LOW Voltage			0.35	0.5	V	I <sub>OL</sub> = 8.0 mA	$V_{IN} = V_{IL}$ or $V_{IH}$ per Truth Table
	land the life of the land of t				20	μΑ	V <sub>CC</sub> = MAX, V <sub>IN</sub>	= 2.7 V
I <sub>IH</sub>	Input HIGH Current				0.1	mA	V <sub>CC</sub> = MAX, V <sub>IN</sub>	<sub>I</sub> = 7.0 V
I <sub>IL</sub>	Input LOW Current			X	-0.4	mA	V <sub>CC</sub> = MAX, V <sub>IN</sub>	<sub>I</sub> = 0.4 V
I <sub>OS</sub>	Short Circuit Current (Note 2	?)	-20		-100	mA	V <sub>CC</sub> = MAX	
1	Dower Supply Current	LS122			11	mΛ	Van MAY	
I <sub>CC</sub>	Power Supply Current	LS123			20	mA	V <sub>CC</sub> = MAX	

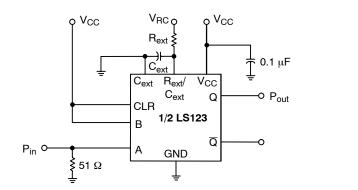
<sup>2.</sup> Not more than one output should be shorted at a time, nor for more than 1 second.

# AC CHARACTERISTICS (T<sub>A</sub> = 25°C, V<sub>CC</sub> = 5.0 V)

			Limits	25		
Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay, A to Q Propagation Delay, A to Q		23	33 45	ns	C <sub>ext</sub> = 0
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay, B to Q Propagation Delay, B to Q		23	44 56	ns	$C_L = 15 \text{ pF}$ $R_{\text{ext}} = 5.0 \text{ k}\Omega$
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay, Clear to Q Propagation Delay, Clear to Q	O . G	28 20	45 27	ns	$R_L = 2.0 \text{ k}\Omega$
t <sub>W min</sub>	A or B to Q	A P	116	200	ns	$C_{\text{ext}} = 1000 \text{ pF, } R_{\text{ext}} = 10 \text{ k}\Omega,$
t <sub>W</sub> Q	A to B to Q	4.0	4.5	5.0	μs	$C_L = 15 \text{ pF}, R_L = 2.0 \text{ k}\Omega$

# AC SETUP REQUIREMENTS (T<sub>A</sub> = 25°C, V<sub>CC</sub> = 5.0 V)

	64 6		Limits			
Symbol	Parameter	Min	Тур	Max	Unit	Test Conditions
t <sub>W</sub>	Pulse Width	40			ns	



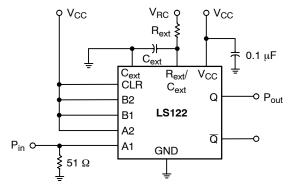


Figure 1.

Figure 2.

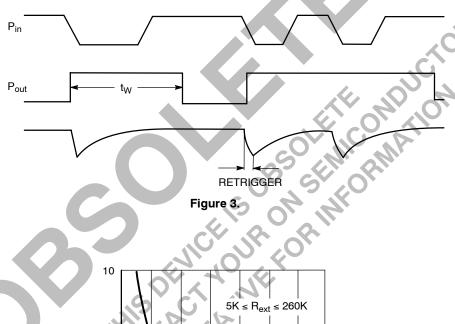


Figure 3.

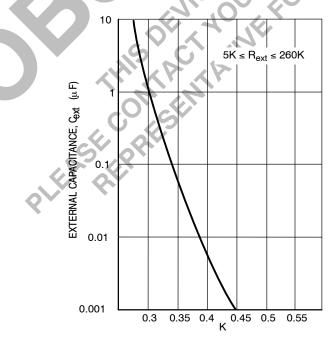
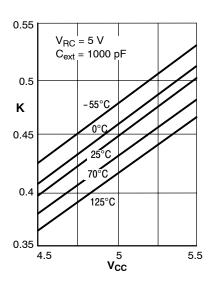
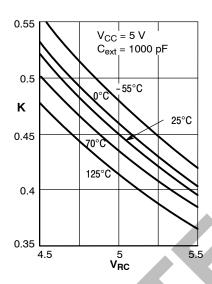


Figure 4.





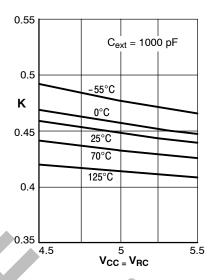


Figure 5. K versus  $V_{\text{CC}}$ 

Figure 6. K versus V<sub>RC</sub>

Figure 7. K versus  $V_{CC}$  and  $V_{RC}$ 

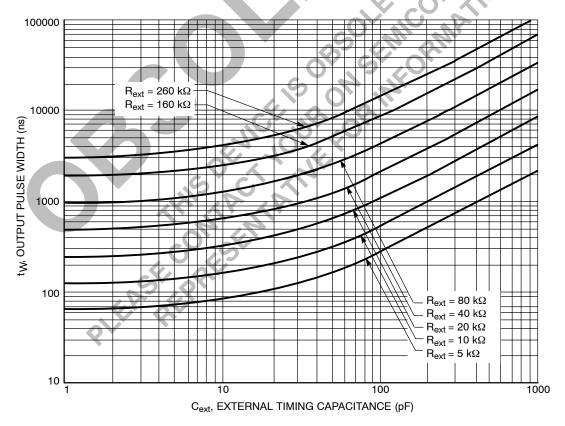


Figure 8.

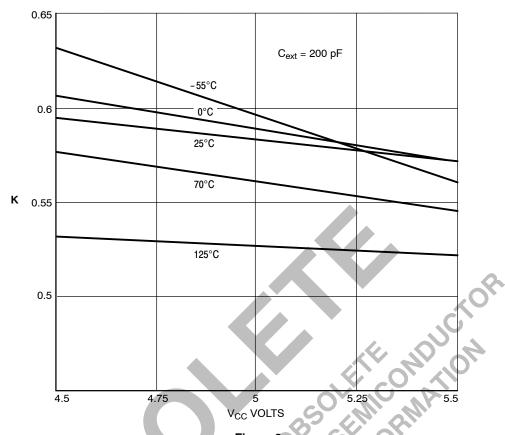


Figure 9.

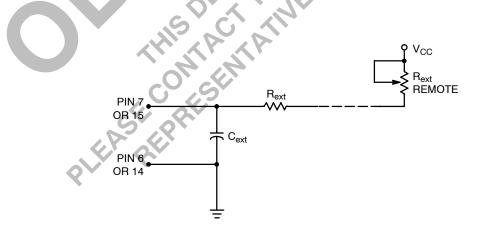


Figure 10. LS123 Remote Trimming Circuit

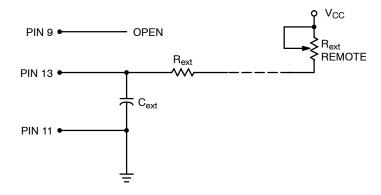
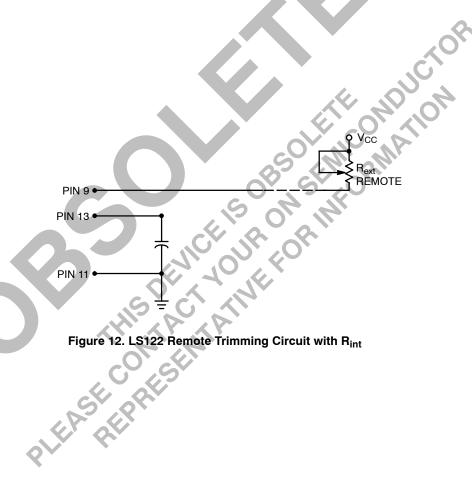


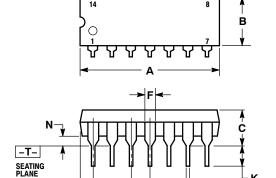
Figure 11. LS122 Remote Trimming Circuit Without R<sub>ext</sub>



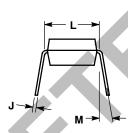
### PACKAGE DIMENSIONS

# **N SUFFIX** PLASTIC PACKAGE CASE 646-06

ISSUE M

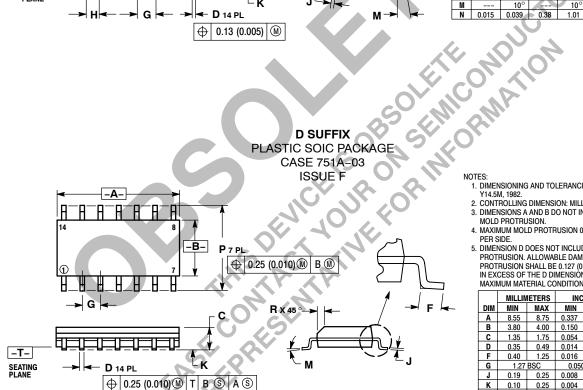


G



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- DIMENSION L TO CENTER OF LEADS WHEN
- FORMED PARALLEL. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
   ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS		
DIM	MIN	MAX	MIN	MAX		
Α	0.715	0.770	18.16	18.80		
В	0.240	0.260	6.10	6.60		
С	0.145	0.185	3.69	4.69		
D	0.015	0.021	0.38	0.53		
F	0.040	0.070	1.02	1.78		
G	0.100	BSC	2.54 BSC			
Н	0.052	0.095	1.32	2.41		
5	0.008	0.015	0.20	0.38		
K	0.115	0.135	2.92	3.43		
L	0.290	0.310	7.37	7.87		
M		10°		10°		
N	0.015	0.030	0.38	1.01		



→ D 14 PL

⊕ 0.13 (0.005) M

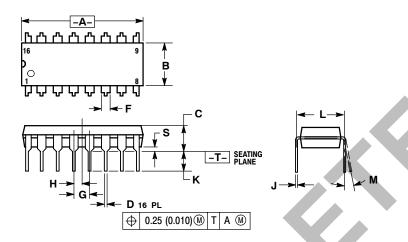
- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- PEH SIDE.

  5. DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION SHALL BE 0.127 (0.005) TOTAL
  IN EXCESS OF THE D DIMENSION AT
  MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	8.55	8.75	0.337	0.344	
В	3.80	4.00	0.150	0.157	
U	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
7	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0 °	7°	0°	7°	
P	5.80	6.20	0.228	0.244	
R	0.25	0.50	0.010	0.019	

# **PACKAGE DIMENSIONS**

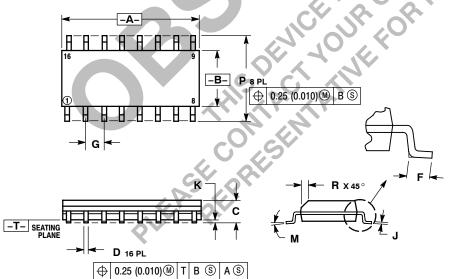
# **N SUFFIX** PLASTIC PACKAGE CASE 648-08 **ISSUE R**



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
- DIMENSION B DOES NOT INCLUDE MOLD FLASH.
   ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.740	0.770	18.80	19.55	
В	0.250	0.270	6.35	6.85	
Ç	0.145	0.175	3.69	4.44	
Ê	0.015	0.021	0.39	0.53	
F	0.040	0.70	1.02	1.77	
G	0.100	BSC	2.54 BSC		
Н	0.050	BSC	1.27 BSC		
7	0.008	0.015	0.21	0.38	
K	0.110	0.130	2.80	3.30	
L	0.295	0.305	7.50	7.74	
M	0°	10°	0 °	10 °	
S	0.020	0.040	0.51	1.01	





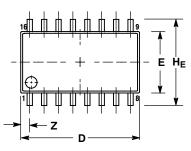
- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION SHALL BE 0.127 (0.005) TOTAL
  IN EXCESS OF THE D DIMENSION AT
  MAXIMUM MATERIAL CONDITION.

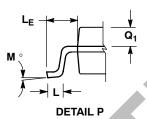
	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

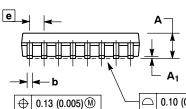
# PACKAGE DIMENSIONS

### **M SUFFIX**

SOEIAJ PACKAGE CASE 966-01 ISSUE O









#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETER
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- 4. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.

  5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α		2.05	-1	0.081	
Α1	0.05	0.20	0.002	0.008	
ь	0.35	0.50	0.014	0.020	
C	0.18	0.27	0.007	0.011	
D	9.90	10.50	0.390	0.413	
E	5.10	5.45	0.201	0.215	
e	1.27	BSC	0.050 BSC		
Η <sub>E</sub>	7.40	8.20	0.291	0.323	
L	0.50	0.85	0.020	0.033	
LE	1.10	1.50	0.043	0.059	
M	0 °	10°	0 °	10°	
$Q_1$	0.70	0.90	0.028	0.035	
Z		0.78		0.031	

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